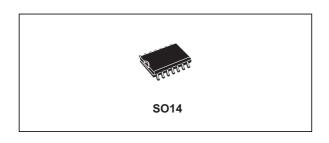


Quad exclusive OR gate

Datasheet - production data



Features

- Medium-speed operation
 t_{PHL} = t_{PLH} = 70 ns (typ) at C_L = 50 pF and
 V_{DD} = 10 V
- Quiescent current specified up to 20 V
- 5 V, 10 V and 15 V parametric ratings
- Input leakage current
 I_I = 100 nA (max) at V_{DD} = 18 V, T_A = 25 °C
- 100% tested for quiescent current
- ESD performance

HBM: 2 kVMM: 200 VCDM: 1 kV

Applications

- Automotive
- Industrial
- Computer
- Consumer

Description

The HCF4070 is a monolithic integrated circuit fabricated in metal oxide semiconductor technology available in an SO14 package.

The HCF4070 contains four independent exclusive OR gates. This device provides the system designer with a means for direct implementation of the exclusive OR gate for applications such as logical comparators, adders/subtractors, parity generators and checkers.

Table 1. Device summary

Order code	Temperature range	Package	Packing	Marking
HCF4070M013TR	–55 °C to +125 °C	SO14	Tape and reel	HCF4070
HCF4070YM013TR ⁽¹⁾	–40 °C to +125 °C	SO14 (automotive grade)	Tape and reer	HCF4070Y

Qualification and characterization according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 and Q002 or equivalent.

Contents HCF4070

Contents

1	Device overview	3
2	Package mechanical data	3
3	Revision history	ı



HCF4070 Device overview

1 Device overview

Figure 1. Pin connections

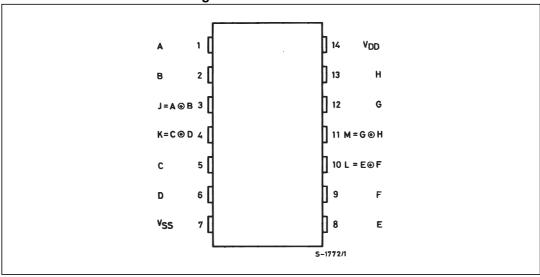
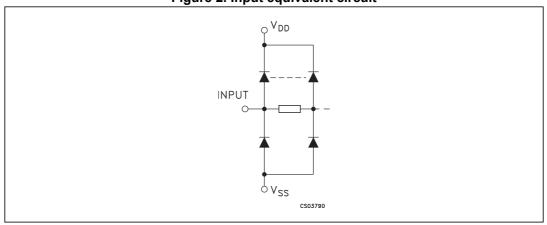


Table 2. Pin description

Pin number	Symbol/name	Function
1, 5, 8, 12	A, C, E, G	Data inputs
2, 6, 9, 13	B, D, F, H	Data inputs
3, 4, 10, 11	J, K, L, M	Data outputs
7	V _{SS}	Negative supply voltage
14	V_{DD}	Positive supply voltage

Figure 2. Input equivalent circuit



Device overview HCF4070

Figure 3. Logic diagram

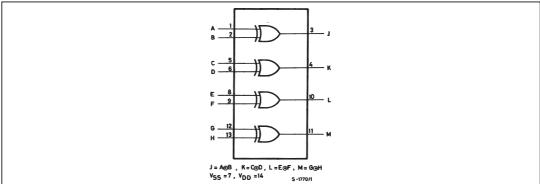


Table 3. Truth table

Inp	Output		
A, C, E, G	B, D, F, H	J, K, L, M	
L	L	L	
L	Н	Н	
Н	L	Н	
Н	Н	L	

Table 4. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DD}	Supply voltage	-0.5 to +22	V
V _I	DC input voltage	-0.5 to V _{DD} + 0.5	V
l _l	DC input current	± 10	mA
В	Power dissipation per package	200	mW
P _D	Power dissipation per output transistor	100	mW
T _{op}	Operating temperature	-55 to +125	°C
T _{stg}	Storage temperature	-65 to +150	°C

Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are relative to the V_{SS} pin voltage.

Table 5. Recommended operating conditions

Symbol	Par	ameter	Value	Unit
V _{DD}	Supply voltage		3 to 20	V
VI	Input voltage		0 to V _{DD}	V
_	Operating temperature	SO14	-55 to 125	°C
Гор	Operating temperature	SO14 (automotive grade)	-40 to 125	°C



HCF4070 Device overview

Table 6. DC specifications

			Test cond	dition					Value				
Sym. Parameter		V _I	v _o	IIOI VDI	V _{DD}	Т,	T _A = 25°C		-40 to 85°C		-55 to 125°C		Unit
		(V)	(V)	(μΑ)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
		0/5			5		0.02	1		30		30	
l _L	Quiescent current	0/10			10		0.02	2		60		60	μΑ
"L	Quiescent current	0/15			15		0.02	4		120		120] μΑ
		0/20			20		0.04	20		600		600	
		0/5		<1	5	4.95			4.95		4.95		
V _{OH}	High-level output voltage	0/10		<1	10	9.95			9.95		9.95		v
	0	0/15		<1	15	14.95			14.95		14.95		
		5/0		<1	5		0.05			0.05		0.05	
V _{OL}	Low-level output voltage	10/0		<1	10		0.05			0.05		0.05] v
	,	15/0		<1	15		0.05			0.05		0.05	
			0.5/4.5	<1	5	3.5			3.5		3.5] v
V _{IH}	High-level input voltage		1/9	<1	10	7			7		7		
	9		1.5/13.5	<1	15	11			11		11		
			4.5/0.5	<1	5			1.5		1.5		1.5	
V _{IL}	Low-level input voltage		9/1	<1	10			3		3		3	v
	9		13.5/1.5	<1	15			4		4		4	
		0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		
I _{OH}	Output drive current	0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		mA
HOI	Output drive current	0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
		0/5	0.4	<1	5	0.44	1		0.36		0.36		
I _{OL}	Output sink current	0/10	0.5	<1	10	1.1	2.6		0.9		0.9		mA
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I _I	Input leakage current	0/18	Any In	out	18		±10 ⁻⁵	±0.1		±1		±1	μА
C _I	Input capacitance		Any In	out			5	7.5					pF

The noise margin for both the "1" and "0" level is: 1 V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V.

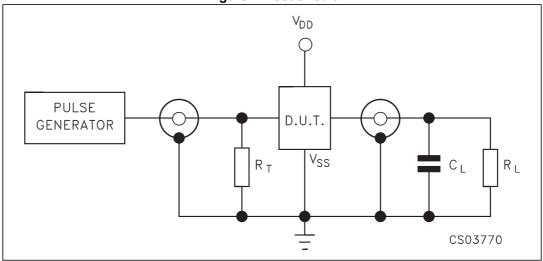
Device overview HCF4070

Table 7. Dynamic electrical characteristics (T_{amb} = 25 °C, C_L = 50 pF, R_L = 200 k Ω , t_r = t_f = 20 ns)

Symbol	Parameter	Test condition	Value ⁽¹⁾			Unit
	Parameter	V _{DD} (V)	Min.	Тур.	Max.	Oille
t _{PLH} t _{PHL} Propaga		5		140	280	
	Propagation delay time	10		70	130	ns
		15		50	100	
		5		100	200	
t _{TLH} t _{THL}	Output transition time	10		50	100	ns
		15		40	80	

^{1.} Typical temperature coefficient for all V_{DD} values is 0.3%/°C.

Figure 4. Test circuit



- 1. $C_L = 50$ pF or equivalent (includes jig and probe capacitance)
- 2. R_L = 200 kΩ
- 3. $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

HCF4070 Device overview

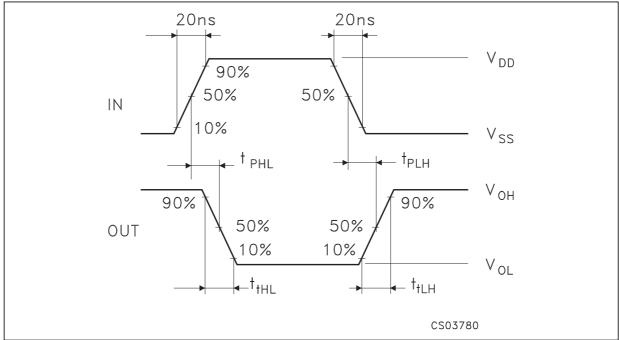


Figure 5. Waveform - propagation delay times (f = 1 MHz; 50% duty cycle)

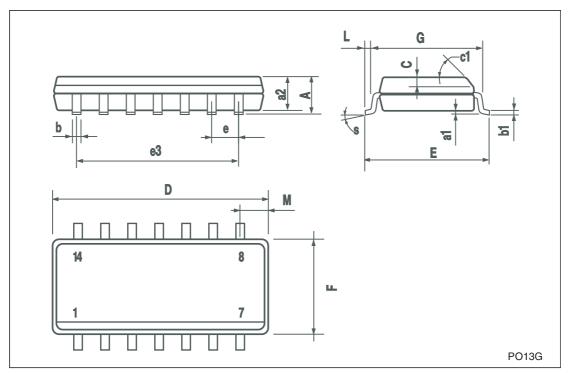
2 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.



SO-14 MECHANIC	CAL	DATA
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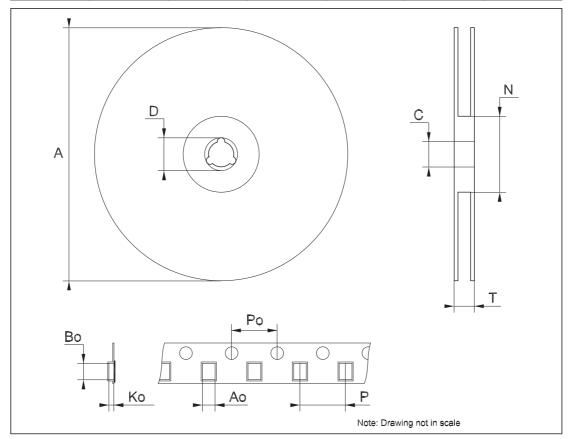
DIM.	mm.											
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.						
Α			1.75			0.068						
a1	0.1		0.2	0.003		0.007						
a2			1.65			0.064						
b	0.35		0.46	0.013		0.018						
b1	0.19		0.25	0.007		0.010						
С		0.5			0.019							
c1			45°	(typ.)								
D	8.55		8.75	0.336		0.344						
Е	5.8		6.2	0.228		0.244						
е		1.27			0.050							
e3		7.62			0.300							
F	3.8		4.0	0.149		0.157						
G	4.6		5.3	0.181		0.208						
L	0.5		1.27	0.019		0.050						
М			0.68			0.026						
S			8° (r	nax.)	•	8° (max.)						





Tape &	Reel	SO-14	MECH	ANICAL	DATA
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DIM.		mm.		inch			
DIW.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А			330			12.992	
С	12.8		13.2	0.504		0.519	
D	20.2			0.795			
N	60			2.362			
Т			22.4			0.882	
Ao	6.4		6.6	0.252		0.260	
Во	9		9.2	0.354		0.362	
Ko	2.1		2.3	0.082		0.090	
Po	3.9		4.1	0.153		0.161	
Р	7.9		8.1	0.311		0.319	



HCF4070 Revision history

3 Revision history

Table 8. Document revision history

Date	Revision	Changes
11-Jun-2012	3	Added Applications on page 1 Updated Table 1: Device summary Revised document presentation, minor textual updates
15-Jun-2012	4	Updated temperature range in <i>Table 1</i> Updated T _{op} in <i>Table 4</i> and <i>5</i>
06-Jan-2014	5	Removed DIP package option Added ESD performance to Features Added packing and marking to Table 1: Device summary Updated footnote 1 of Table 1: Device summary

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